

DATA SHEET

BUW84; BUW85 Silicon diffused power transistors

Product specification
Supersedes data of February 1996
File under Discrete Semiconductors, SC06

1997 Aug 14

Silicon diffused power transistors

BUW84; BUW85

DESCRIPTION

High-voltage, high-speed, glass-passivated NPN power transistor in a SOT82 package.

APPLICATIONS

- Converters
- Inverters
- Switching regulators
- Motor control systems
- Switching applications.

PINNING

PIN	DESCRIPTION
1	base
2	collector; connected to mounting base
3	emitter

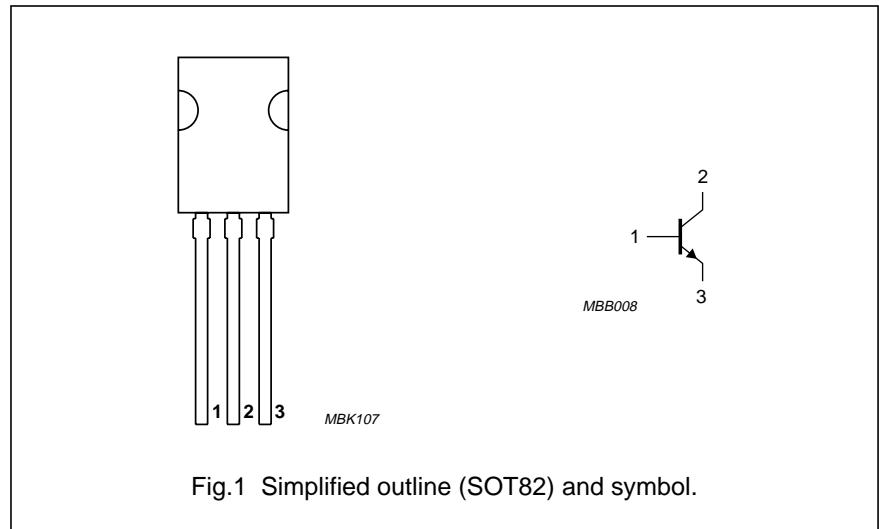


Fig.1 Simplified outline (SOT82) and symbol.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	-	800	V
	BUW84				
V_{CEO}	collector-emitter voltage	open base	-	400	V
	BUW85				
V_{CEsat}	collector-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 200\text{ mA};$ see Fig.7	-	1	V
I_C	collector current (DC)	see Figs 4 and 5	-	2	A
I_{CM}	collector current (peak value)	see Figs 4 and 5	-	3	A
P_{tot}	total power dissipation	$T_{mb} \leq 25\text{ }^\circ\text{C};$ see Fig.8	-	50	W
t_f	fall time	resistive load; see Fig.11	0.4	-	μs

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-mb}$	thermal resistance from junction to mounting base	2.1	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient in free air	100	K/W

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	collector-emitter peak voltage	$V_{BE} = 0$	–	800	V
	BUW84			1000	V
V_{CEO}	collector-emitter voltage	open base	–	400	V
	BUW84			450	V
V_{EBO}	emitter-base voltage	open collector	–	5	V
I_C	collector current (DC)	see Figs 4 and 5	–	2	A
I_{CM}	collector current (peak value)	$t_p = 2$ ms; see Figs 4 and 5	–	3	A
I_B	base current (DC)		–	0.75	A
I_{BM}	base current (peak value)		–	1	A
I_{BM}	base current (reversed; peak value)	turn-off current	–	–1	A
P_{tot}	total power dissipation	$T_{mb} \leq 25$ °C; see Fig.8	–	50	W
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

CHARACTERISTICS $T_j = 25$ °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{CEOsust}$	collector-emitter sustaining voltage	$I_C = 100$ mA; $I_{Boff} = 0$; $L = 25$ mH; see Figs 2 and 3	400	–	–	V
	BUW84		450	–	–	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.3$ A; $I_B = 30$ mA; see Fig.7	–	–	0.8	V
		$I_C = 1$ A; $I_B = 200$ mA; see Fig.7	–	–	1	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 1$ A; $I_B = 200$ mA	–	–	1.1	V
I_{CES}	collector-emitter cut-off current	$V_{CEM} = V_{CEMSmax}$; $V_{BE} = 0$; note 1	–	–	200	μ A
		$V_{CEM} = V_{CEMSmax}$; $V_{BE} = 0$; $T_j = 125$ °C; note 1	–	–	1.5	mA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5$ V; $I_C = 0$	–	–	1	mA
h_{FE}	DC current gain	$V_{CE} = 5$ V; $I_C = 5$ A; see Fig.10	15	–	–	
		$V_{CE} = 5$ V; $I_C = 100$ mA; see Fig.10	20	50	100	
f_T	transition frequency	$V_{CE} = 10$ V; $I_C = 200$ mA; $f = 1$ MHz	–	20	–	MHz

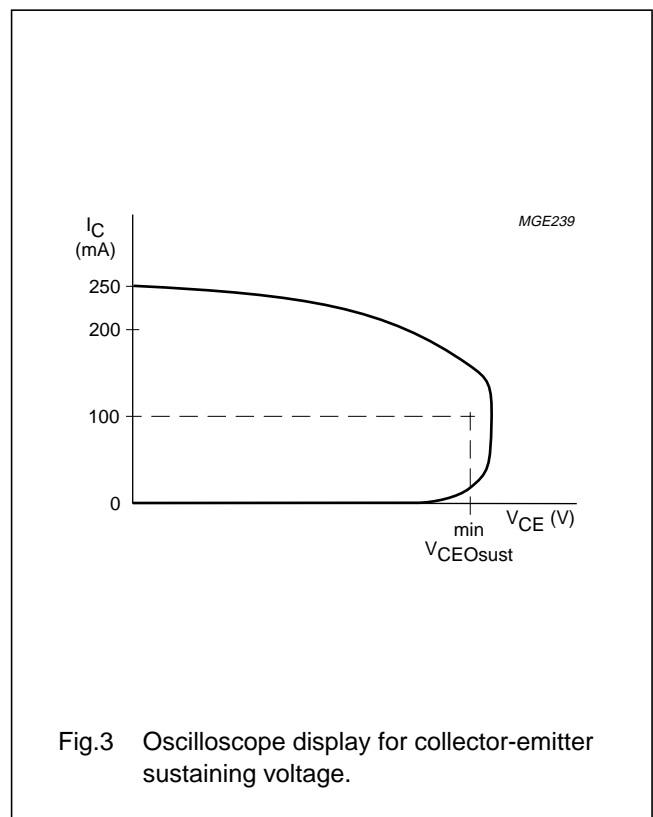
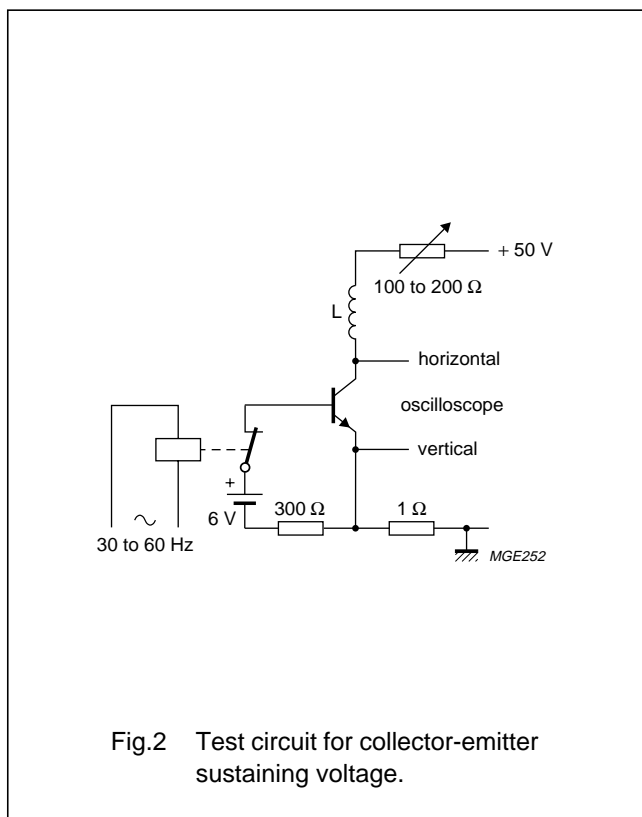
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SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Switching times in horizontal deflection circuit (see Fig.11)						
t_{on}	turn-on time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	0.2	0.5	μs
t_s	storage time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	2	3.5	μs
t_f	fall time	$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}$	–	0.4	–	μs
		$I_{Con} = 1\text{ A}; I_{Bon} = 200\text{ mA}; I_{Boff} = -400\text{ mA}; V_{CC} = 250\text{ V}; T_{mb} = 95\text{ }^\circ\text{C}$	–	–	1.4	μs

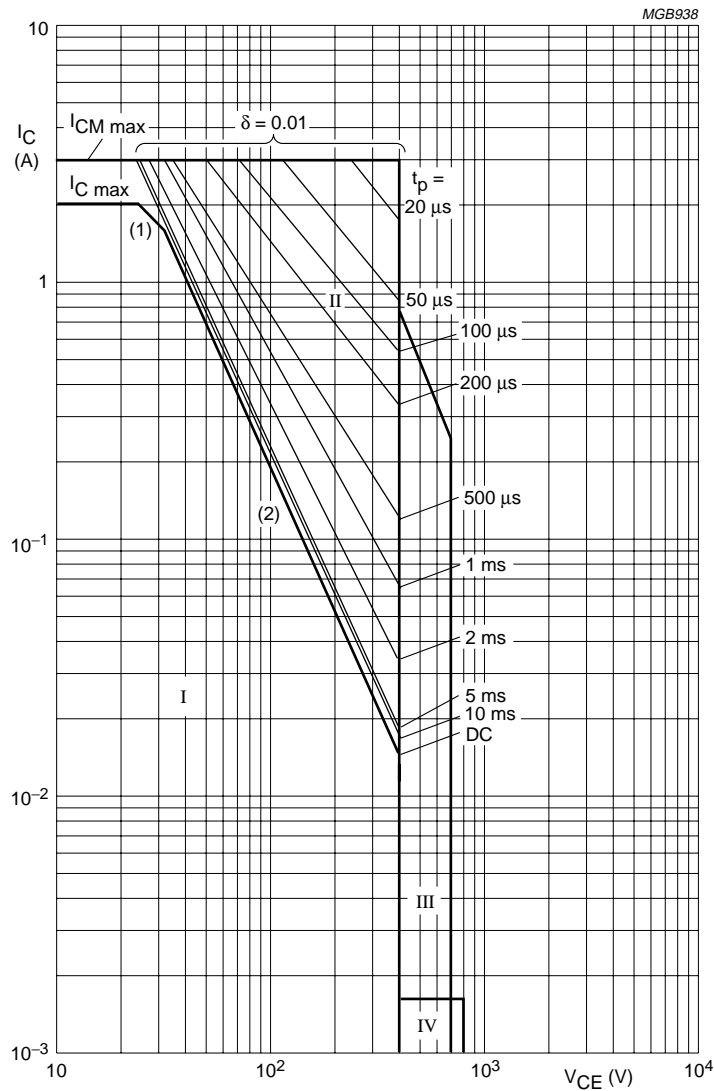
Note

1. Measured with a half-sinewave voltage (curve tracer).



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BUW84.

$T_{mb} \leq 25$ °C.

I - Region of permissible DC operation.

II - Permissible extension for repetitive pulse operation.

III - Area of permissible operation during turn-on in single transistor converters, provided $R_{BE} \leq 100 \Omega$ and $t_p \leq 0.6 \mu$ s.

IV - Repetitive pulse operation in this region is permissible provided $V_{BE} \leq 0$ and $t_p \leq 2$ ms.

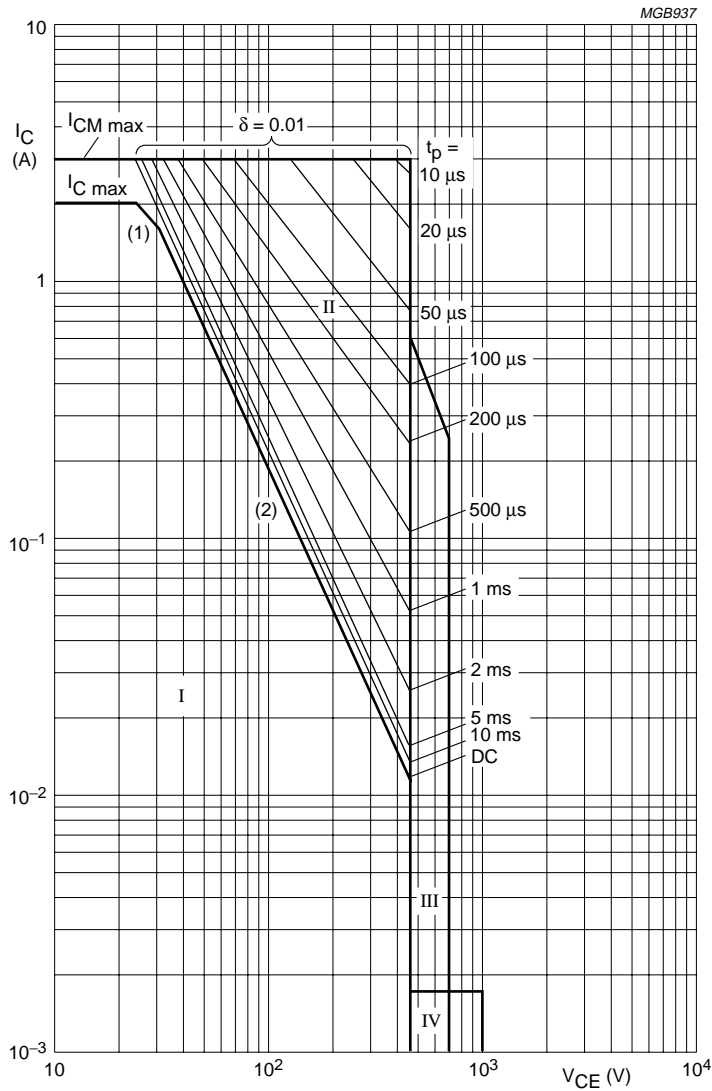
(1) $P_{tot\ max}$ line.

(2) Second breakdown limits.

Fig.4 Forward bias SOAR.

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BUW85.

$T_{mb} \leq 25\text{ }^{\circ}\text{C}.$

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IV - Repetitive pulse operation in this region is permissible provided $V_{BE} \leq 0$ and $t_p \leq 2\ \text{ms}.$

(1) $P_{tot\ max}$ line.

(2) Second breakdown limits.

Fig.5 Forward bias SOAR.

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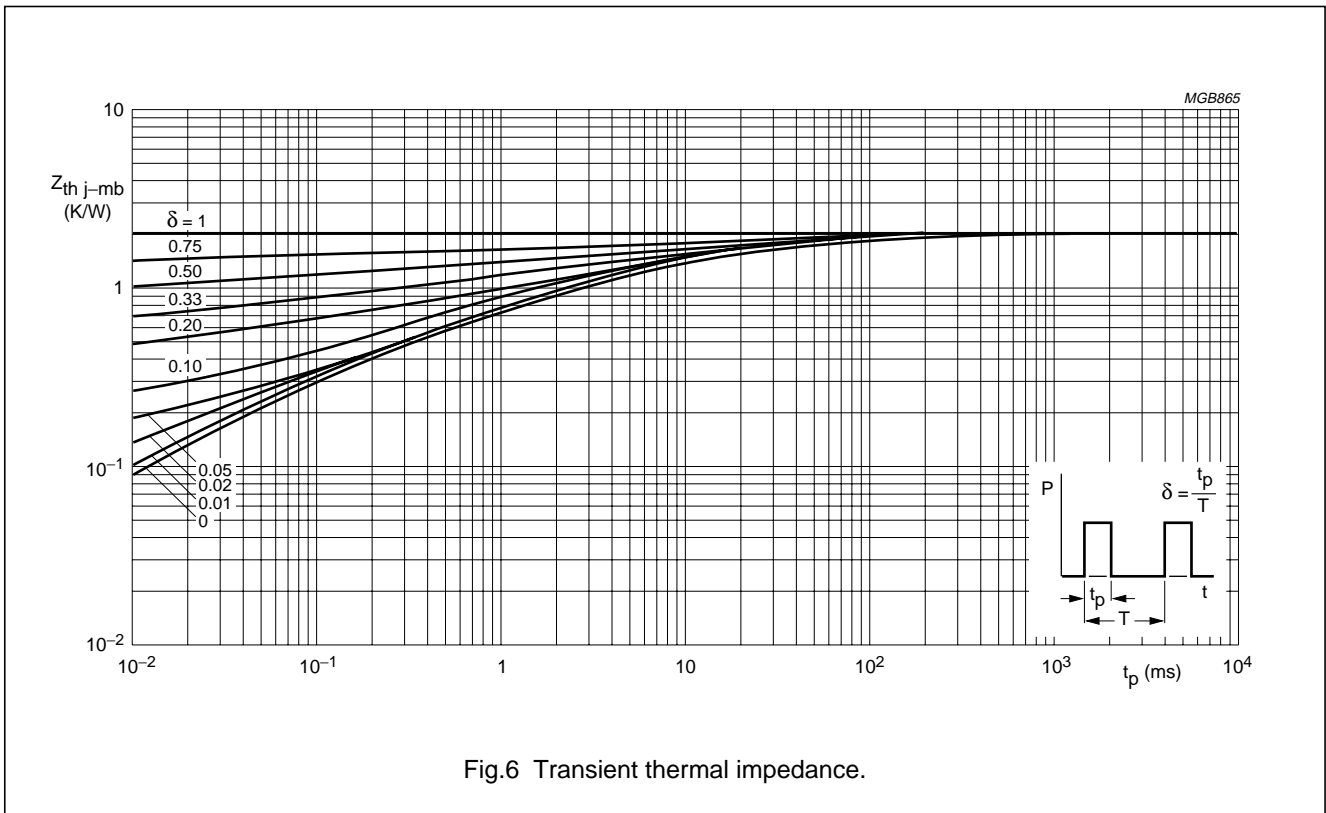


Fig.6 Transient thermal impedance.

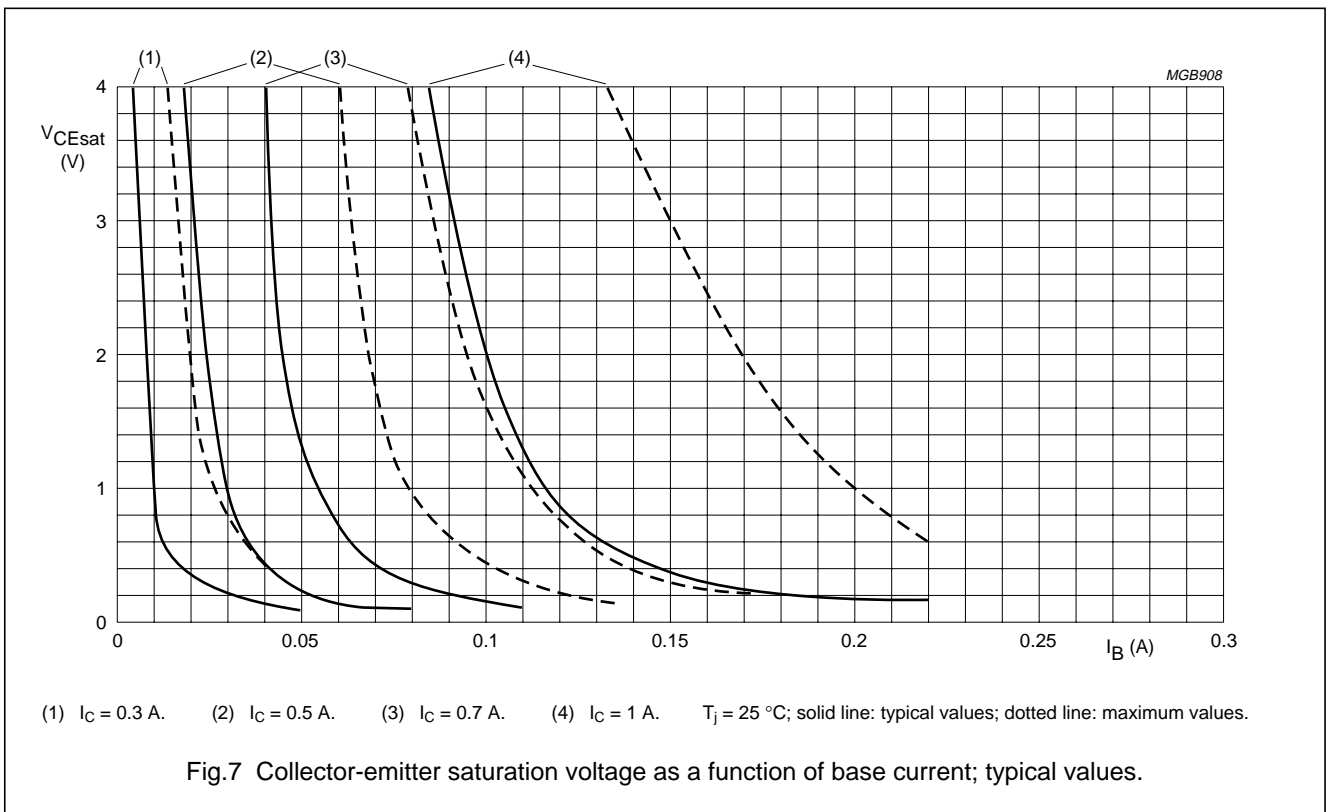
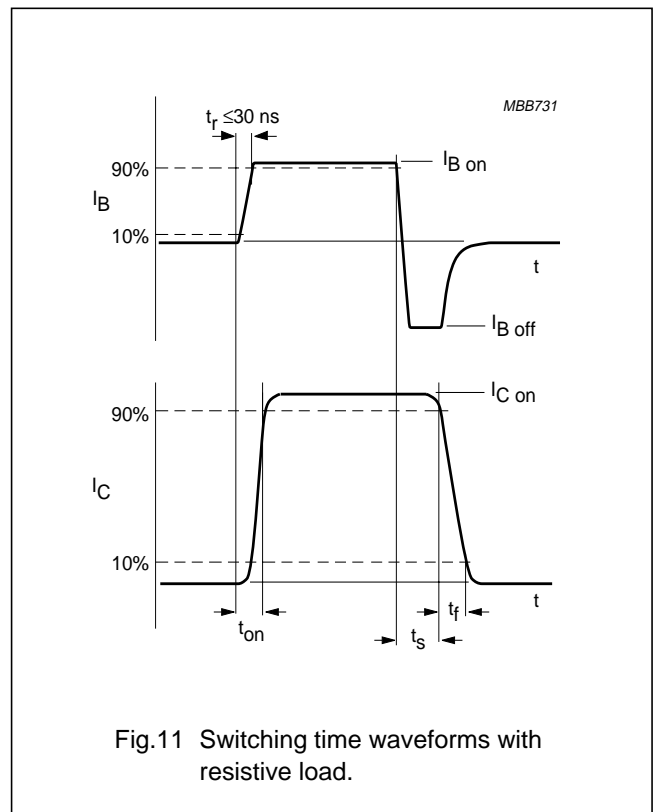
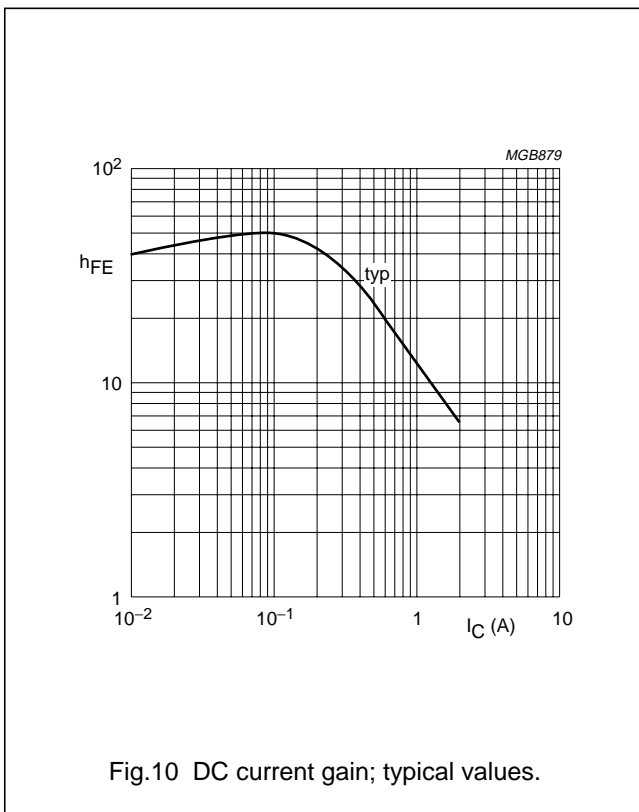
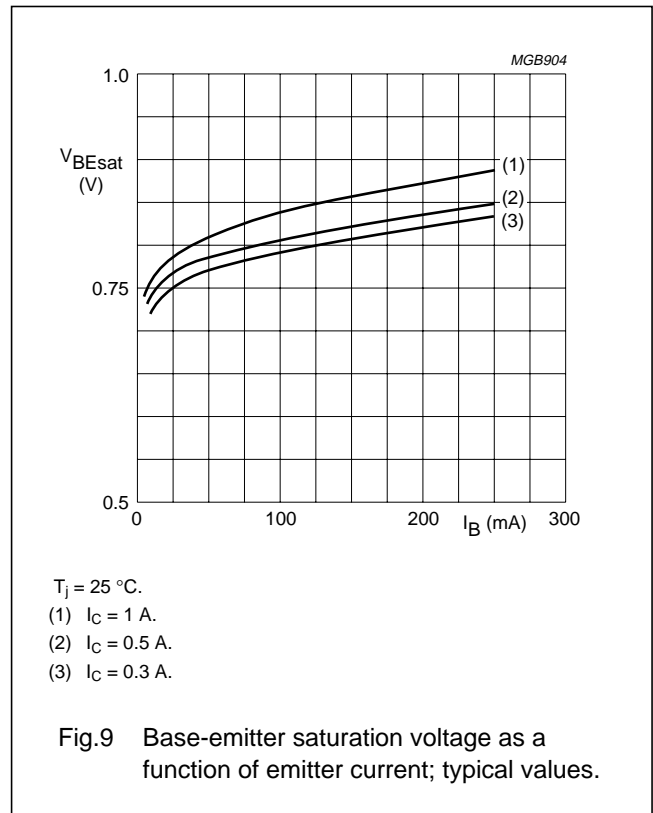
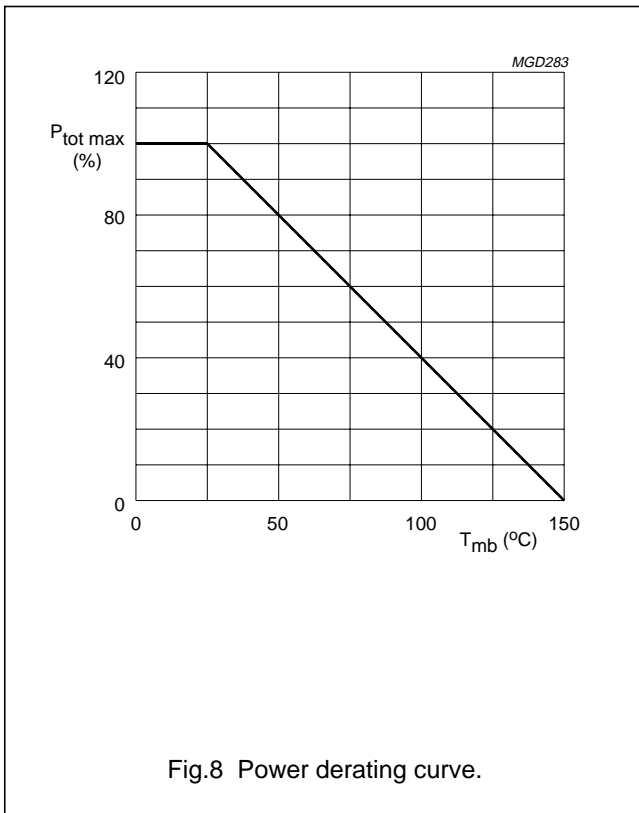


Fig.7 Collector-emitter saturation voltage as a function of base current; typical values.

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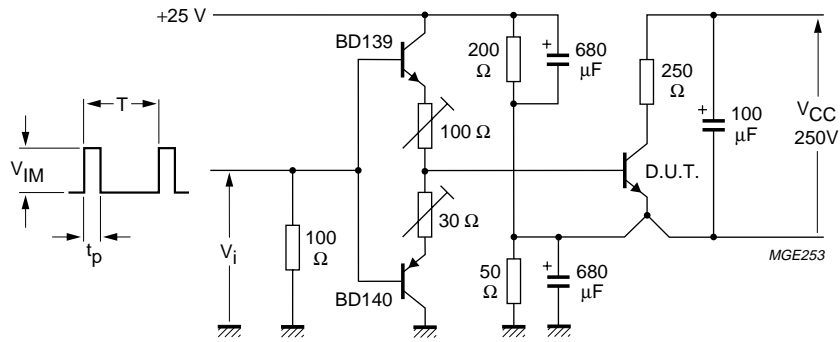


Fig.12 Test circuit resistive load.

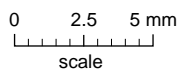
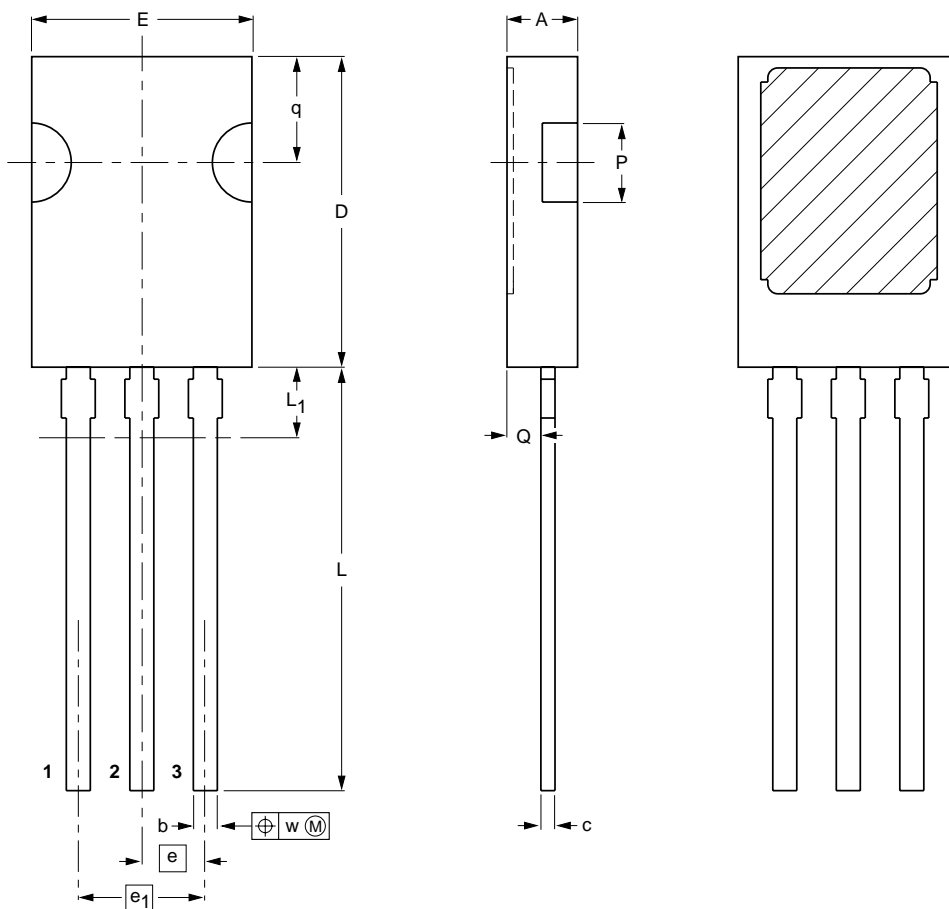
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PACKAGE OUTLINE

Plastic single-ended package; 3 leads (in-line)

SOT82



DIMENSIONS (mm are the original dimensions)

UNIT	A	b	c	D	E	e	e ₁	L	L ₁ ⁽¹⁾ max.	P	Q	q	w
mm	2.8 2.3	0.88 0.65	0.58 0.47	11.1 10.5	7.8 7.2	2.29	4.58	16.5 15.3	2.54	3.1 2.5	1.5 0.9	3.9 3.5	0.254

Note

1. Terminal dimensions within this zone are uncontrolled to allow for body and terminal irregularities.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT82						97-06-11

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DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Printed in The Netherlands

137067/00/01/pp12

Date of release: 1997 Aug 14

Document order number: 9397 750 02722

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